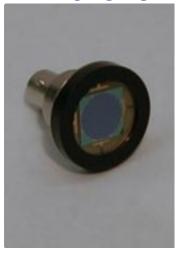
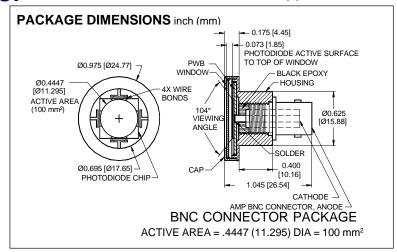
PHOTONIC DETECTORS INC.

Silicon Photodiode, Blue Enhanced Photovoltaic Type PDB-V112





FEATURES

- Blue enhanced
- Low noise
- High shunt resistance
- High response

DESCRIPTION

Large area, instrumentation grade, blue enhanced silicon photodiode. Designed for low noise photovoltaic applications.

Packaged in a BNC connector package.

APPLICATIONS

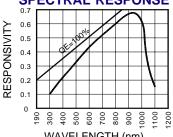
- Instrumentation
- Power meters
- Colorimeters
- Laser power meters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		75	V
TS	Storage Temperature	-20	+70	°C
ТО	Operating Temperature Range	-10	+60	°C
TS	Soldering Temperature*	N/A	N/A	°C
lmax	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ISC	Short Circuit Current	H = 100 fc, 2850 K	0.9	1.2		mA
ID	Dark Current	H = 0, VR = 10 mV		200	335	nA
RSH	Shunt Resistance	H = 0, VR = 10 mV	30	50		ΜΩ
TC RSH	RSH Temp. Coefficient	H = 0, VR = 10 mV		-8		%/℃
CJ	Junction Capacitance	H = 0, VR = 0V**		10,000	12,000	pF
Irange	Spectral Application Range	Spot Scan	350		1100	nm
lp	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	Ι= 10 μΑ	20	30		V
NEP	Noise Equivalent Power	VR = 10 mV @ Peak		2x10 ⁻¹⁴		W/ √Hz
tr	Response Time	RI = 1 KO VR = 0V		2000		nS